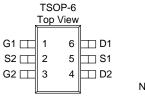
N & P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low r_{DS(on)} and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low $r_{DS(\text{on})}$ provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY							
$V_{DS}(V)$ $r_{DS(on)}(\Omega)$ $I_{D}(A)$							
20	$0.047 @ V_{GS} = 4.5V$	4.1					
20	$0.055 @ V_{GS} = 2.5V$	3.8					
-20	$0.079 @ V_{GS} = -4.5V$	-3.2					
-20	$0.110 @ V_{GS} = -2.5V$	-2.7					







ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
	Parameter	Symbol	N-Channel	P-Channel	Uni	
	Drain-Source Voltage	V_{DS}	20	-20	Ι,,	

Drain-Source Voltage	V_{DS}	20	-20	V	
Gate-Source Voltage			±8	±8	V
	$T_A=25^{\circ}C$	Ι_	4.1	-3.2	
Continuous Drain Current ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	I_{D}	3.3	-2.6	Α
Pulsed Drain Current ^b	I_{DM}	8	-8		
Continuous Source Current (Diode Con	I_S	1.05	-1.05	A	
D : a	$T_A=25^{\circ}C$	$\frac{T_{A}=25^{\circ}C}{T_{A}=70^{\circ}C}P_{D}$		1.15	
Power Dissipation ^a	$T_A=70^{\circ}C$	P_{D}	0.7		W
Operating Junction and Storage Temper	ting Junction and Storage Temperature Range T _J , T _{stg} -55 to 150		o 150	°C	

THERMAL RESISTANCE RATINGS									
Parameter	Symbol	N-Channel		P-Channel		Unit			
rarameter		Тур	Max	Тур	Max	Unit			
National Location to Austriant	t <= 10 sec	R _{thJA}	93	110	93	110	°C/W		
Maximum Junction-to-Ambient ^a	Steady State	KthJA	130	150	130	150	C/W		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

AM3524C

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)									
Parameter	Parameter Symbol Test Conditions Limits Ch Min Typ May								
	Symbol	Test Conditions	Ch	Min	Тур	Max	Unit		
Static									
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$, $I_{D} = 250 \text{ uA}$	N	0.4			V		
Cure Timeshola Younge	, G8(m)	$V_{GS} = V_{DS}$, $I_{D} = -250 \text{ uA}$	P	-0.4		100	·		
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = 8 \text{ V}$	N P			100	uA		
		$V_{DS} = 0 \text{ V}, V_{GS} = -8 \text{ V}$ $V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$	N			1			
		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$	P			-1	uA		
Zero Gate Voltage Drain Current	I_{DSS}	,	N			10	uA		
		$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{I} = 55^{\circ}\text{C}$ $V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{I} = 55^{\circ}\text{C}$	P			-10			
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	N	5			Α		
	D(oil)	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	P N	-5		0.047	7.1		
_		V _{GS} = 4.5 V, I _D = 4.1 A V _{GS} = -4.5 V, I _D = -3.2 A	P			0.047			
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$V_{GS} = 2.5 \text{ V, ID} = 3.8 \text{ A}$	N			0.075	Ω		
		$V_{GS} = -2.5 \text{ V}, I_{D} = -2.7 \text{ A}$	P			0.110	1		
Forward Tranconductance ^A	σ.	$V_{DS} = 5 \text{ V}, I_{D} = 4.1 \text{ A}$	N		10		S		
1 of ward 1 fanconductance	g_{fs}	$V_{DS} = -5 \text{ V}, I_{D} = -3.2 \text{ A}$	P		5		3		
Diode Forward Voltage ^A	V_{SD}	$I_S = 1.05 \text{ A}, V_{GS} = 0 \text{ V}$ $I_S = -1.05 \text{ A}, V_{GS} = 0 \text{ V}$	N P		0.80		S		
Dynamic ^b		$I_S - 1.03 \text{ A}, V_{GS} - 0 \text{ V}$	r		-0.83				
			N		7.5		1		
Total Gate Charge	Qg	N-Channel	P		3.8		nC		
Gate-Source Charge	Qgs	$V_{DS} = 15V, V_{GS} = 4.5V, I_{D} = 4.1A$	N		0.6				
Gate Source charge	∠g ₃	P-Channel	P		0.6				
Gate-Drain Charge	Q_{gd}	VDS=-15V, VGS=-4.5V, ID=-3.2A	N		1.0				
2			P N		1.5				
Turn-On Delay Time	td(on)	N-Chaneel	P		5	1			
D. T.		$V_{DD}=15V, V_{GS}=4.5V, I_{D}=1A$,	N		12				
Rise Time	$t_{\rm r}$	$R_{GEN}=15\Omega$,	P		15		C		
Turn-Off Delay Time	td(off)	P-Channel	N		13		nS		
Tuin-On Delay Time	га(оп)	VDD=-15V, VGS=-4.5V, ID=-1A	P		20				
Fall-Time	t_{f}	$R_{GEN}=15\Omega$	N		7	ļ			
	• • • • • • • • • • • • • • • • • • • •		P		20				

Notes

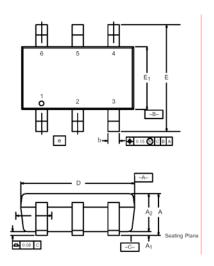
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

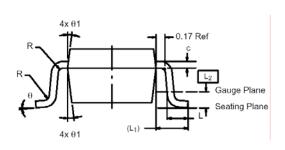
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Analog Power AM3524C

Package Information

TSOP-6: 6LEAD





	MIL	LIMET	ERS	ı	NCHES	;	
Dim	Min	Nom	Max	Min	Min Nom		
Α	0.91	-	1.10	0.036	_	0.043	
Α1	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.84	_	1.00	0.033	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.004 0.006		
D	2.95	3.05	3.10	0.116	0.116 0.120		
Е	2.70	2.85	2.98	0.106 0.112		0.117	
E ₁	1.55	1.65	1.70	0.061 0.065		0.067	
е	1.00 BSC			0.0394 BSC			
L	0.35	_	0.50	0.014	0.014 –		
L ₁		0.60 Ref		0.024 Ref			
L ₂		0.25 BSC		0.010 BSC			
R	0.10	_	_	0.004	-	_	
θ	0°	4°	8°	0°	4°	8°	
θ_1		7° Nom		7° Nom			